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#### (54) CONTACT FEATURES OF SEMICONDUCTOR DEVICES

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#### (57)ABSTRACT

A method of fabricating a semiconductor device includes recessing an upper portion of a first dielectric layer disposed over a conductive feature. The method includes filling the recessed upper portion with a second dielectric layer to form a void embedded in the second dielectric layer. The method includes etching the second dielectric layer and the first dielectric layer to form a contact opening that exposes at least a portion of the conductive feature using the void to vertically align at least a lower portion of the contact opening with the conductive feature. The method includes filling the contact opening with a conductive material to form a contact feature electrically coupled to the conductive feature.

